

SMALL SIGNAL SWITCHING DIODE

REVERSE VOLTAGE : 60 V
CURRENT: 0.15 A

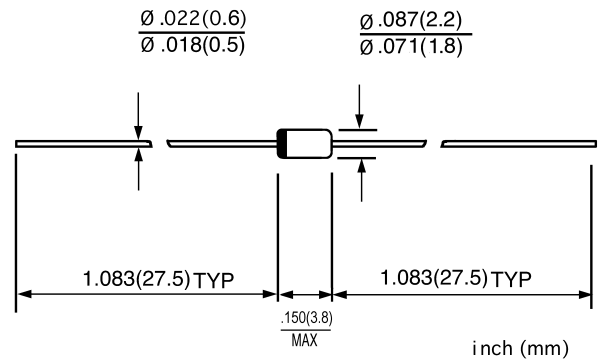
FEATURES

- ◇ Silicon epitaxial planar diode
- ◇ High speed switching diode
- ◇ 500 mW power dissipation

MECHANICAL DATA

- ◇ Case: DO-35, glass case
- ◇ Polarity: Color band denotes cathode
- ◇ Weight: 0.004 ounces, 0.13 grams

DO-35(GLASS)



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

MAXIMUM RATINGS

		1S2076A	UNITS
Reverse voltage	V_R	60	V
Peak reverse voltage	V_{RM}	70	V
Average forward rectified current half wave rectification with resist.load @ $T_A=25^\circ\text{C}$ and $f \geq 50\text{Hz}$	I_{AV}	150	mA
Forward surge current @ $t < 1\text{s}$ and $T_J=25^\circ\text{C}$	I_{FSM}	1.0	A
Power dissipation @ $T_A=25^\circ\text{C}$	P_{tot}	250 ¹⁾	mW
Junction temperature	T_J	175	°C
Storage temperature range	T_{STG}	-55 --- +175	°C

1)Valid provided that leads at a distance of 8 mm from case are kept at ambient temperature.

ELECTRICAL CHARACTERISTICS

		MIN	TYP	MAX	UNITS
Forward voltage at $I_F=10\text{mA}$	V_F	-	-	0.8	V
Leakage current @ $V_R=30\text{V}$	I_R	-	-	0.1	μA
Capacitance @ $V_F=V_R=1\text{V}, f=1\text{MHz}$	C_J	-	-	3.0	pF
Reverse recovery time from $I_F=I_R=10\text{mA}$ to $I_r=1\text{mA}$	t_{rr}	-	-	8.0	ns

**FIG.1 – ADMISSIBLE POWER DISSIPATION
VERSUS AMBIENT TEMPERATURE**

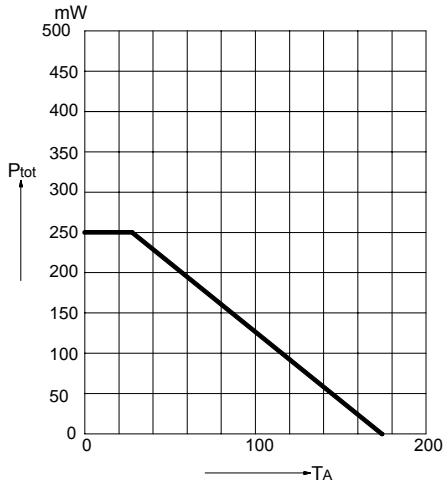


FIG.2 – FORWARD CHARACTERISTICS

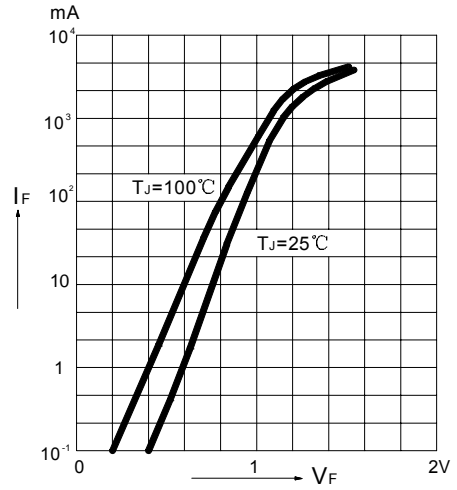


FIG.3 – ADMISSIBLE REPETITIVE PEAK FORWARD CURRENT VERSUS PULSE DURATION

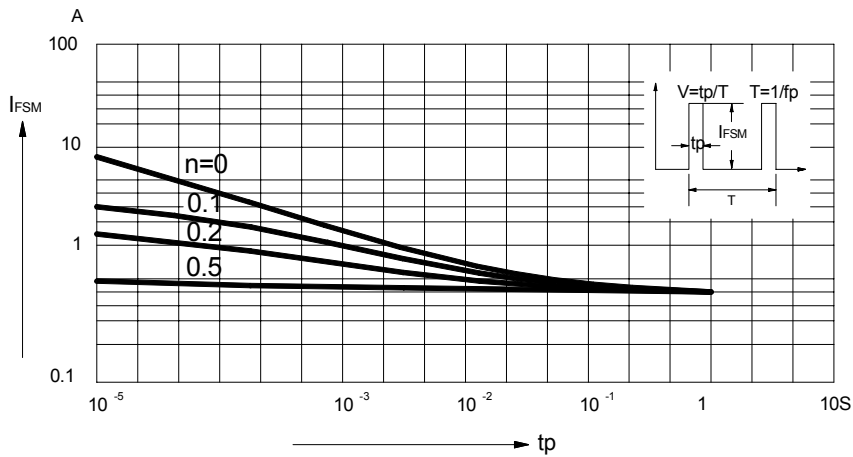


FIG.4 – RECTIFICATION EFFICIENCY MEASUREMENT CIRCUIT

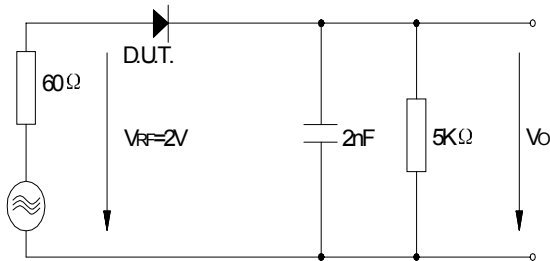


FIG.5 – RELATIVE CAPACITANCE VERSUS VOLTAGE

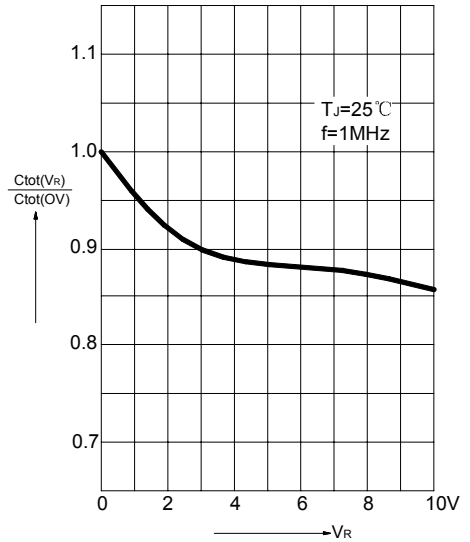


FIG.6 – LEAKAGE CURRENT VERSUS JUNCTION TEMPERATURE

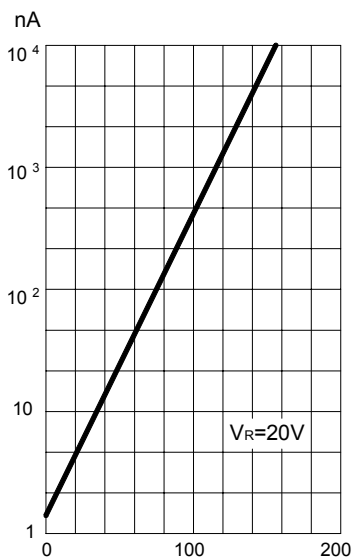


FIG.7 – DYNAMIC FORWARD RESISTANCE VERSUS FORWARD CURRENT

